

B1
amended

adding an inert gas element to an upper layer of the second semiconductor film;
gettering the material for promoting crystallization into the upper layer of the second semiconductor film.

66. (Amended) A method of manufacturing a semiconductor device comprising:

providing a crystalline semiconductor film comprising silicon over a substrate, said crystalline semiconductor film containing metallic element;

forming a barrier layer over the crystalline semiconductor film;

forming a second semiconductor film over the barrier layer;

forming a third semiconductor film comprising an inert gas element over the second semiconductor film;

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gettering the metallic element into the third semiconductor film to remove or reduce the amount of the metallic element within the crystalline semiconductor film; and
removing the second semiconductor film and the third semiconductor film.

67. (Amended) A method of manufacturing a semiconductor device comprising:

providing a crystalline semiconductor film comprising silicon over a substrate, said crystalline semiconductor film containing metallic element;

forming a barrier layer over the crystalline semiconductor film;

forming a second semiconductor film over the barrier layer;

adding an inert gas element to an upper layer of the second semiconductor film;

gettering the metallic element into the upper layer of the second semiconductor film to remove or reduce the amount of the metallic element within the crystalline semiconductor film; and

removing the second semiconductor film.

Please add the following new claims 78-80 as follows:

--78. A method of manufacturing a semiconductor device comprising the steps of:

providing a crystalline semiconductor film comprising silicon over a substrate, said crystalline semiconductor film containing metallic element;

forming a semiconductor film over the crystalline semiconductor film;

adding an inert element into the semiconductor film;

gettering the metallic element into the semiconductor film to remove or reduce the amount of the metallic element within the crystalline semiconductor film.

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79. A method of manufacturing a semiconductor device according to claim 78, wherein the inert element is added into an upper surface of the semiconductor film.

80. A method of manufacturing a semiconductor device according to claim 78, wherein the semiconductor film comprises a first semiconductor film and a second semiconductor film comprising an inert gas element on the first semiconductor film. --
